

ABSTRACT OF THE DISCLOSURE

A nitride semiconductor structure is provided which greatly improves ohmic characteristics by repairing process damage by regrowing an
5 indium-containing p-type nitride semiconductor on a p-type nitride semiconductor having the process damage. In addition, a nitride semiconductor bipolar transistor is provided which can greatly improve its current gain and offset voltage. The structure
10 includes an indium-containing p-type nitride semiconductor layer (8) on a p-type nitride semiconductor (2) processed by etching. The bipolar transistor, which has a base layer composed of a p-type nitride semiconductor, has an
15 indium-containing p-type InGaN base layer (8) regrown on a surface of a p-type InGaN base layer (2) exposed by etching an emitter layer (1).